What is claimed is:

1. A method of depositing a wiring thin film on a semiconductor substrate, comprising the steps of:

depositing a Ti film; and

depositing an Al-Si-Cu film on the Ti film at a temperature of at least 400℃.

2. A method of depositing a wiring thin film on a semiconductor substrate, comprising the steps of:

depositing a Ti film;

depositing an Al-Si-Cu film on the Ti film; and

annealing the semiconductor substrate at a temperature of at least 400℃.

3. The method of depositing a wiring thin film on a semiconductor substrate as disclosed in claim 1, comprising the steps of:

depositing a Ti film;

depositing an Al_3Ti film on the Ti film;

and depositing an Al-Si-Cu film on the Al_3Ti film at a temperature of at least 400℃.

4. The method of depositing a wiring thin film on a semiconductor substrate as disclosed in claim 2, comprising the steps of:

depositing a Ti film;

depositing an Al_3Ti film on the Ti film;

depositing an Al-Si-Cu film on the Al_3Ti film; and

annealing the semiconductor substrate at a temperature of at least 400℃.

5. A method of depositing a wiring thin film on a semiconductor substrate, comprising the steps of:

depositing a Ti film;

depositing an Al-Si-Cu film on the Ti film; and

depositing an Al_3Ti film on the Al-Si-Cu film.

6. The method of depositing a wiring thin film on a semiconductor substrate as disclosed in claim 5, comprising the steps of:

depositing a Ti film;

depositing an Al-Si-Cu film on the Ti film; and

depositing an Al_3Ti film on the Al-Si-Cu film; and

annealing the semiconductor substrate at a temperature of at least 400℃.

7. The method of depositing a wiring thin film on a semiconductor substrate as disclosed in claim 5, comprising the steps of:

depositing a Ti film;

depositing an Al-Si-Cu film on the Ti film; and

depositing an on the Al-Si-Cu film at a temperature of at least 400℃.